NSN 5962-01-040-4354

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Between 0.750 inches and 0.795 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.120 inches and 0.195 inches

Maximum Power Dissipation Rating:

625.0 milliwatts

Operating Tempurature Range:

+0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Cheyenne aircraft model 427m

Features Provided:

Bipolar and hermetically sealed and high speed and monolithic and positive outputs and programmable and programmed and w/buffered output and w/decoded output and w/disable and w/enable and w/storage and 3-state output

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

-0-001-ag joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

11530-278539 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

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Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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